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SEMICONDUCTOR



ESD



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MOV

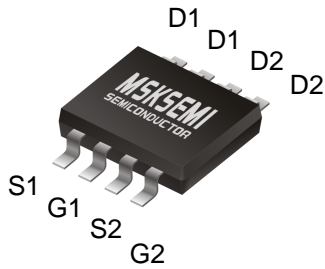


GDT

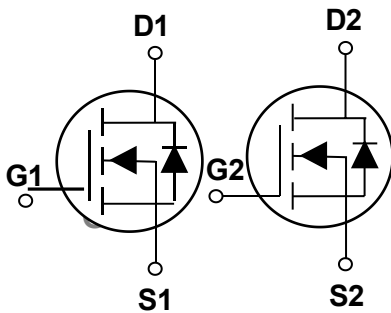


PLED

Product data sheet



SOP-8



### Features

- -30 V, -5.5A,  $R_{DS(ON)} = 45m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

### Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-30V	45mΩ	-5.5A

Absolute Maximum Ratings  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	-5.5	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	-3.48	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-22	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	2.1	W
	Power Dissipation – Derate above 25C	0.017	W/ C
$T_{STG}$	Storage Temperature Range	-55 to 150	C
$T_J$	Operating Junction Temperature Range	-55 to 150	C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	60	C/ W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	45	55	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	---	65	80	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.6	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	---	3.5	---	S

**Dynamic and switching Characteristics**

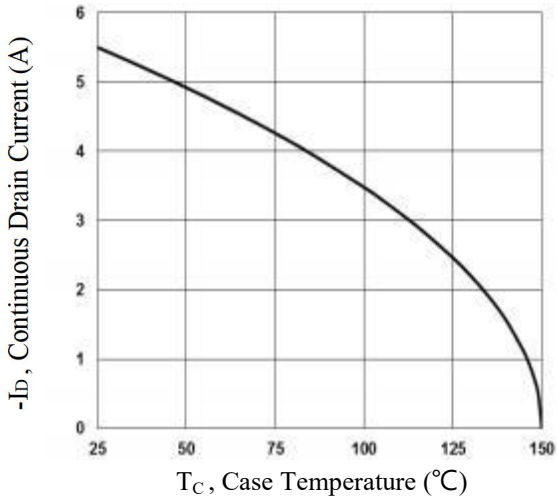
Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	5.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	2	---	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	2.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω I <sub>D</sub> =-1A	---	3.4	---	ns
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	10.8	---	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		---	26.9	---	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	6.9	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz	---	560	---	pF
C <sub>oss</sub>	Output Capacitance		---	55	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	40	---	

**Drain-Source Diode Characteristics and Maximum Ratings**

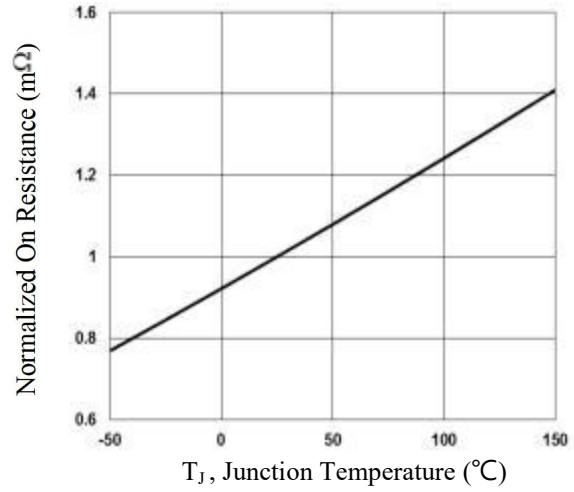
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-5.5	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-11	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

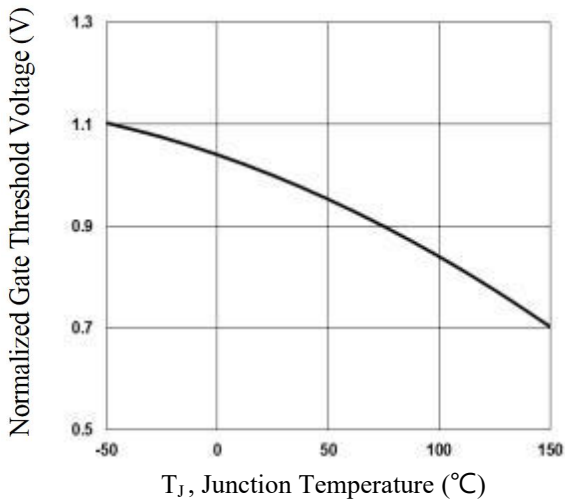
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



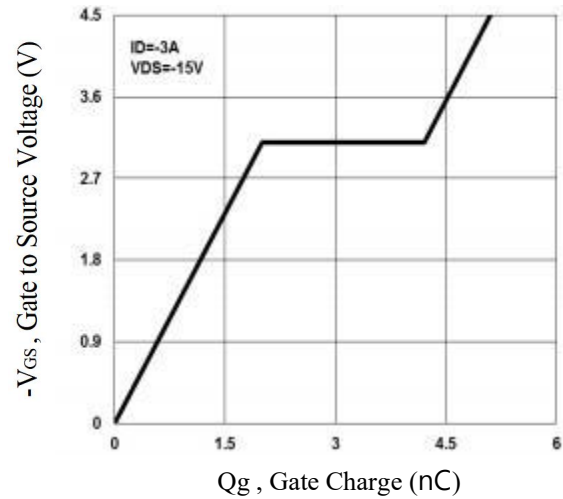
**Fig.1 Continuous Drain Current vs. T<sub>C</sub>**



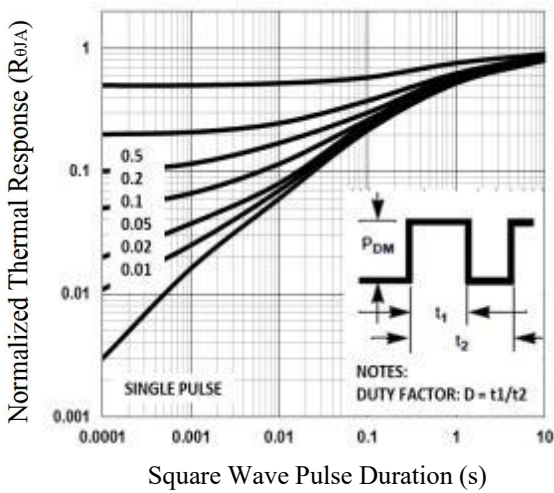
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



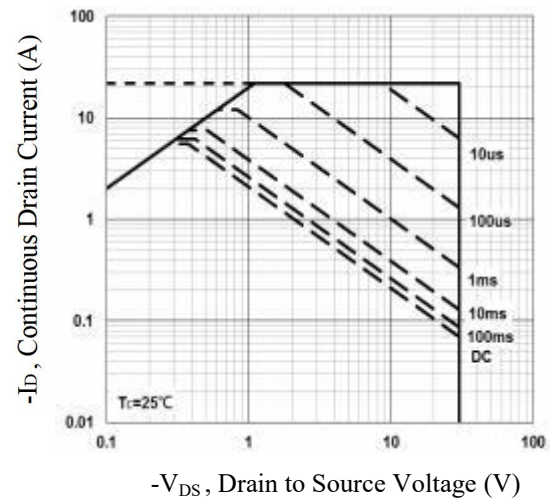
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>J</sub>**



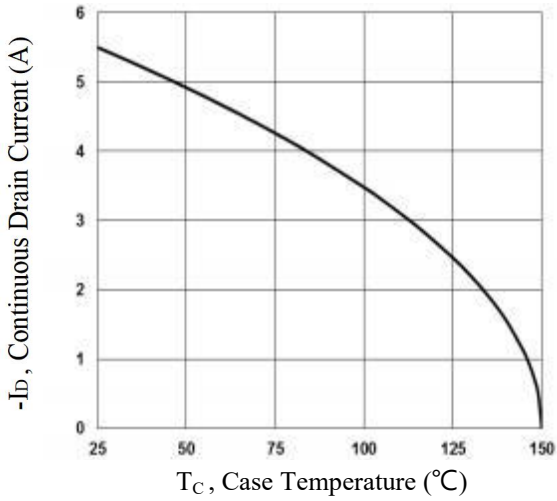
**Fig.4 Gate Charge Waveform**



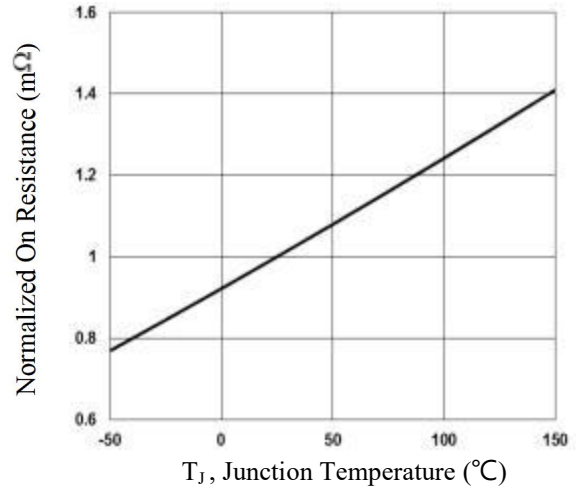
**Fig.5 Normalized Transient Impedance**



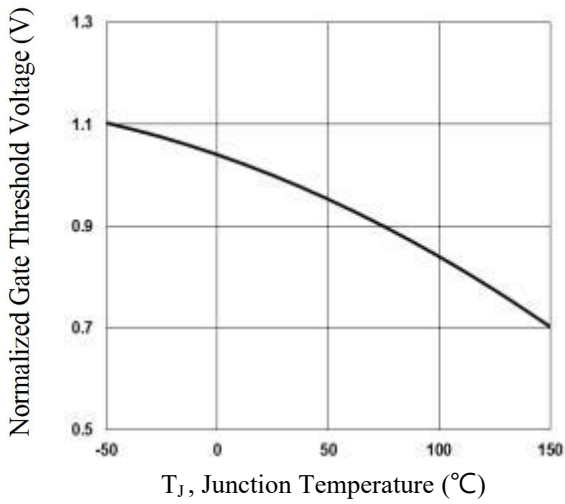
**Fig.6 Maximum Safe Operation Area**



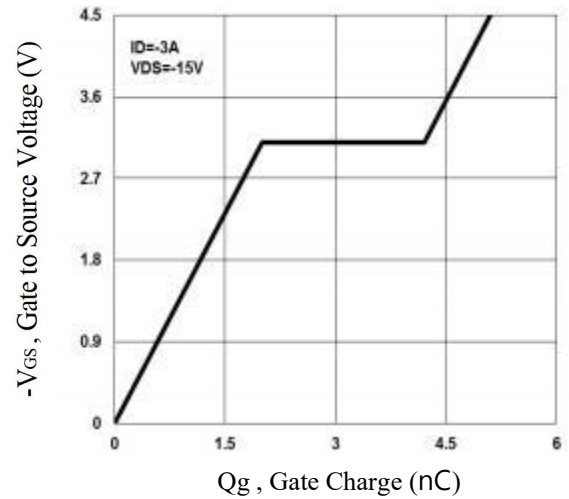
**Fig.1 Continuous Drain Current vs. T<sub>C</sub>**



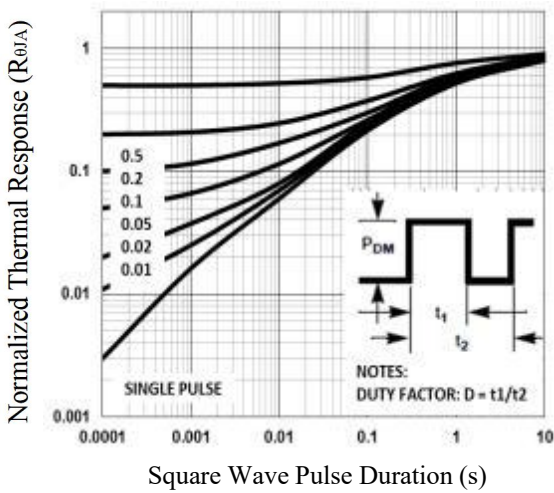
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



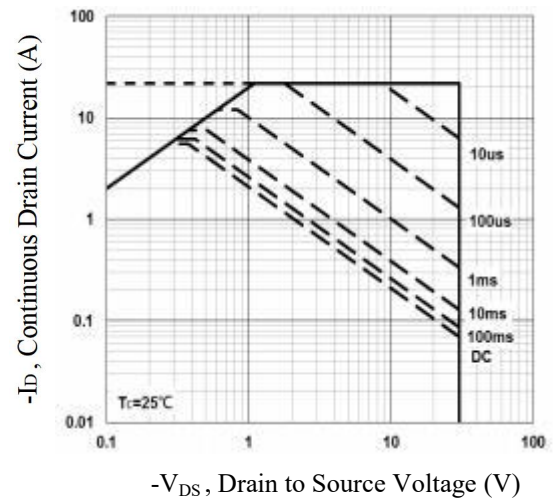
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>J</sub>**



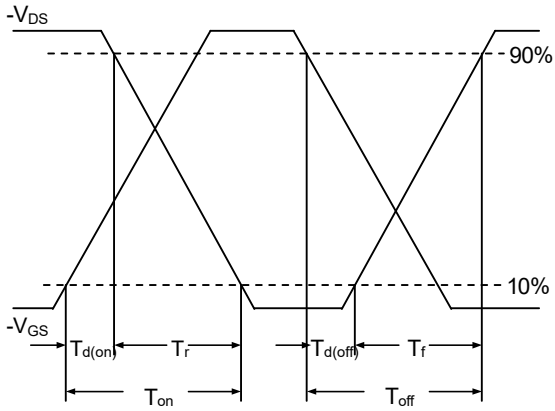
**Fig.4 Gate Charge Waveform**



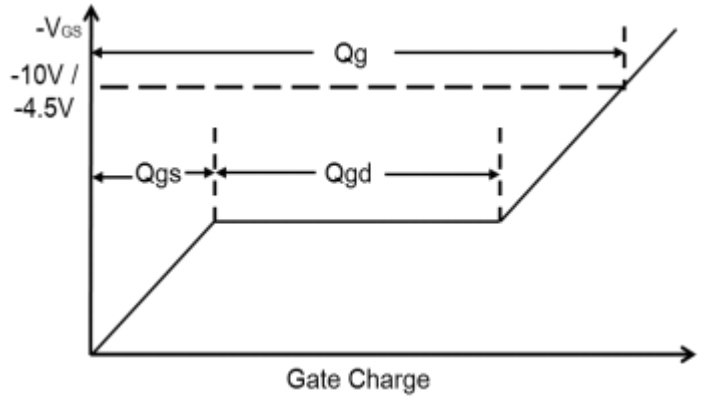
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

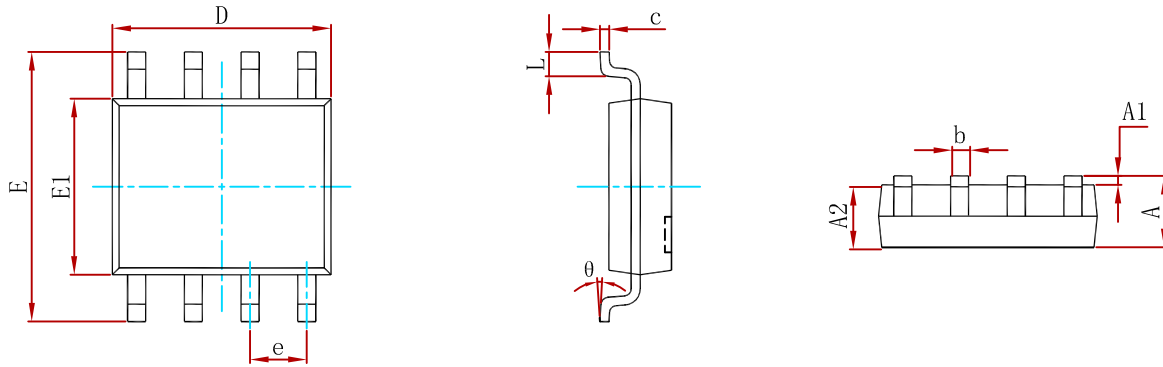


**Fig.7 Switching Time Waveform**



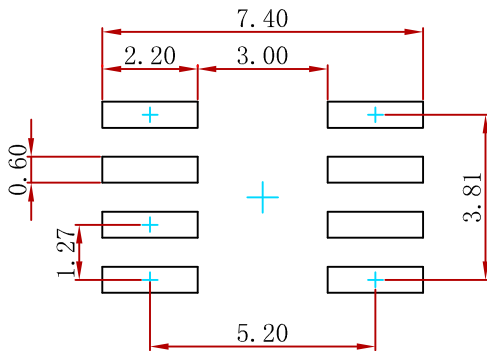
**Fig.8 Gate Charge Waveform**

**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ± 0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
4953	SOP-8	3000

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